

ABSTRACT

5 The present invention provides a ceramic substrate which
can keep a sufficiently large breakdown voltage even if the pore
diameter of its maximum pore is 50 μm or less to be larger than
that of conventional ceramic substrates, can give a large
fracture toughness value because of the presence of pores, can
resist thermal impact, and can give a small warp amount at high
temperature. The ceramic substrate of the present invention
10 is a ceramic substrate for a semiconductor-producing/examining
device having a conductor formed on a surface of the ceramic
substrate or inside the ceramic substrate, wherein: the substrate
is made of a non-oxide ceramic containing oxygen; and the pore
diameter of the maximum pore thereof is 50 μm or less.

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